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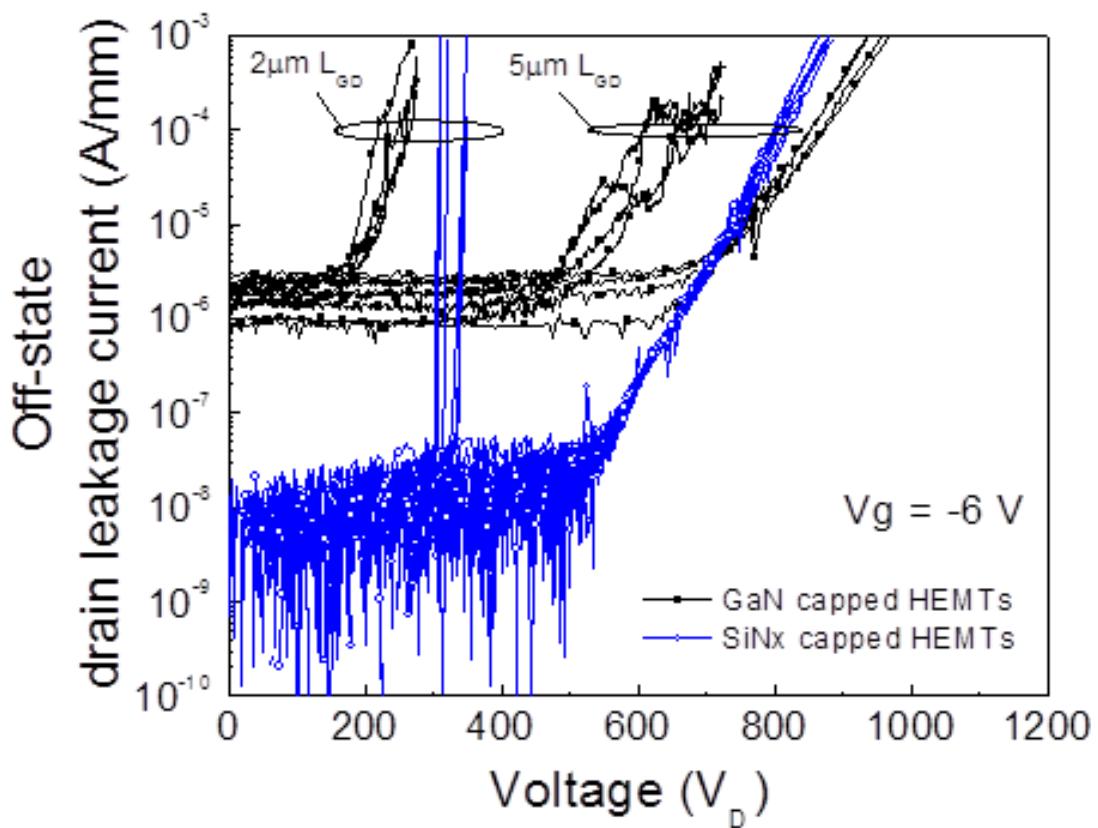


Fig. 1. 3-terminal breakdown curves for GaN- and SiNx capped HEMTs. The off-state drain leakage current is reduced significantly.